

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions and listings of claims in the application:

LISTING OF CLAIMS

1.(Currently Amended) A method of forming a metal line layer in a semiconductor device, comprising:

- depositing a first, second and third conductive layers on a semiconductor substrate;
- depositing an insulating film on the third conductive layer;
- depositing and patterning a photosensitive material on the insulating film;
- etching portions of the insulating film, the third and second conductive layers using the photosensitive material as a mask;
- removing the photosensitive material;
- forming a side wall oxide film on the side walls of the second conductive layer by reacting the second conductive layer with ozone; and
- etching portions of the first conductive layer using the insulating film as a hard mask.

2.(Previously Presented) A method of forming a metal line layer in a semiconductor device according to claim 1, wherein the second conductive layer is made of aluminum (Al).

3.(Previously Presented) A method of forming a metal line layer in a semiconductor device according to claim 1, wherein the metal line layer is formed by laminating a first Ti/TiN layer, an Al layer and a second Ti/TiN layer in this order, and the side wall oxide film is an Al₂O₃ film.

4.(Currently Amended) A method of forming a metal line in a semiconductor memory device according to claim 1, wherein the ~~insulating film~~, the third, ~~and~~ second and first conductive layers are dry-etched using activated plasma comprising $\text{Cl}_2/\text{BCl}_3/\text{N}_2$ gas.

5.(Canceled)

6.(Previously Presented) A method of forming a metal line in a semiconductor device according to claim 1, wherein the insulating film is a nitride film.

7.(Previously Presented) A method of forming a metal line in a semiconductor device according to claim 1, wherein the insulating film is etched by means of a dry etching process using activated plasma comprising a combination of $\text{CHF}_3/\text{CF}_4/\text{Ar}$ or C_xF_y (where x, y are natural numbers)/ O_2/Ar gas.

8. (Canceled)

9.(New) A method of forming a metal line layer in a semiconductor device, comprising:

- depositing a first, second and third conductive layers on a semiconductor substrate;
- depositing an insulating film on the third conductive layer;
- dry etching portions of the insulating film, the third and second conductive layers using activated plasma, whereby a portions of side walls of the second conductive layer are over-etched by the plasma ions;
- forming a side wall oxide film on the side walls of the second conductive layer by reacting the second conductive layer with ozone; and
- etching portions of the first conductive layer using the insulating film as a hard mask.

10.(New) A method of forming a metal line layer in a semiconductor device according to claim 9, wherein the first conductive layer is made of Ti/TiN layer, the second conductive layer is made of aluminum (Al), and the third conductive layer is made of Ti/TiN layer.

11.(New) A method of forming a metal line layer in a semiconductor device according to claim 9, wherein the side wall oxide film is an Al_2O_3 film.

12.(New) A method of forming a metal line in a semiconductor device according to claim 9, wherein the insulating film is a nitride film.

13.(New) A method of forming a metal line in a semiconductor device according to claim 9, wherein the insulating film is etched by means of a dry etching process using activated plasma comprising a combination of $\text{CHF}_3/\text{CF}_4/\text{Ar}$ or C_xF_y (where x, y are natural numbers)/ O_2/Ar gas.

14.(New) A method of forming a metal line in a semiconductor memory device according to claim 9, wherein the third and second conductive layers are dry-etched using activated plasma comprising $\text{Cl}_2/\text{BCl}_3/\text{N}_2$ gas.